

Yuh-Renn Wu

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Electro-Optical Numerical Modeling for the Design of UVA Nitride-Based Vertical-Cavity Surface-Emitting Laser Diodes. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-6.	1.9	0
2	Hole mobility behavior in Al-gradient polarization-induced p-type AlGaN grown on GaN template. Applied Physics Letters, 2022, 120, .	1.5	5
3	Design of Monolayer MoS ₂ Nanosheet Transistors for Low-Power Applications. IEEE Transactions on Electron Devices, 2022, 69, 358-363.	1.6	3
4	Efficiency and Forward Voltage of Blue and Green Lateral LEDs with V-shaped Defects and Random Alloy Fluctuation in Quantum Wells. Physical Review Applied, 2022, 17, .	1.5	13
5	Study on the effect of size on InGaN red micro-LEDs. Scientific Reports, 2022, 12, 1324.	1.6	41
6	Study of the Factors Limiting the Efficiency of Vertical-Type Nitride- and AlInGaP-Based Quantum-Well Micro-LEDs. Processes, 2022, 10, 489.	1.3	2
7	Investigating the high field transport properties of Janus WSe and MoSe by DFT analysis and Monte Carlo simulations. Journal of Applied Physics, 2022, 131, .	1.1	4
8	Vertical hole transport through unipolar InGaN quantum wells and double heterostructures. Physical Review Materials, 2022, 6, .	0.9	2
9	Study of Carrier Scattering and Mobility in Monolayer MoTe ₂ and WTe ₂ by First-Principle Analysis. , 2022, , .		0
10	Influences of dielectric constant and scan rate on hysteresis effect in perovskite solar cell with simulation and experimental analyses. Scientific Reports, 2022, 12, 7927.	1.6	12
11	Improved Vertical Carrier Transport for Green III-Nitride LEDs Using $\text{In}_{0.78}\text{Ga}_{0.22}\text{Tj}$ Alloy Quantum Barriers. Physical Review Applied, 2022, 17, .	1.3	9
12	Studies of 2D Bulk and Nanoribbon Band Structures in Mo _x W _{1-x} S ₂ Alloy System Using Full sp ³ d ⁵ Tight-Binding Model. Physica Status Solidi (B): Basic Research, 2021, 258, 2000375.	0.7	1
13	Deep Source Metal Trenches in GaN-On-Si HEMTs for Relieving Current Collapse. IEEE Journal of the Electron Devices Society, 2021, 9, 557-563.	1.2	4
14	Wearable Devices Made of a Wireless Vertical-Type Light-Emitting Diode Package on a Flexible Polyimide Substrate with a Conductive Layer. ACS Applied Electronic Materials, 2021, 3, 979-987.	2.0	9
15	CMOS-compatible GaN HEMT on 200mm Si-substrate for RF application. , 2021, , .		0
16	Giant gauge factor of Van der Waals material based strain sensors. Nature Communications, 2021, 12, 2018.	5.8	62
17	Calculation of Field Dependent Mobility in MoS ₂ and WS ₂ with Multi-Valley Monte Carlo Method. , 2021, , .		3
18	Modeling dislocation-related reverse bias leakage in GaN p-n diodes. Semiconductor Science and Technology, 2021, 36, 075001.	1.0	2

#	ARTICLE	IF	CITATIONS
19	Investigation of Electrical and Optical Properties of AlGaInP Red Vertical Micro-Light-Emitting Diodes With Cu/Invar/Cu Metal Substrates. IEEE Transactions on Electron Devices, 2021, 68, 2818-2822. Three-Dimensional Modeling of Minority-Carrier Lateral Diffusion Length Including Random Alloy Fluctuations in (T_j ETQq0 0 0 rgBT /Overlock 10 Tf 5	1.6	10
20		1.5	14
21	Influences of Random Alloy Fluctuation to the Efficiency of μ LED and Optimization of Efficiency with Vertical Type Contact. , 2021, , .		0
22	Graphene/SnS ₂ van der Waals Photodetector with High Photoresponsivity and High Photodetectivity for Broadband 365–2240 nm Detection. ACS Applied Materials & Interfaces, 2021, 13, 47198-47207.	4.0	18
23	The 2020 UV emitter roadmap. Journal Physics D: Applied Physics, 2020, 53, 503001.	1.3	289
24	Theoretical and experimental investigations of vertical hole transport through unipolar AlGaIn structures: Impacts of random alloy disorder. Applied Physics Letters, 2020, 117, .	1.5	13
25	Characterization of semi-polar ($\overline{2}1$) InGaIn microLEDs. Scientific Reports, 2020, 10, 15966.	1.6	7
26	Bistriazoles with a Biphenyl Core Derivative as an Electron-Favorable Bipolar Host of Efficient Blue Phosphorescent Organic Light-Emitting Diodes. ACS Applied Materials & Interfaces, 2020, 12, 49895-49904.	4.0	13
27	A 3D simulation comparison of carrier transport in green and blue c-plane multi-quantum well nitride light emitting diodes. Journal of Applied Physics, 2020, 128, 235703.	1.1	9
28	Analysis of the triplet exciton transfer mechanism at the heterojunctions of organic light-emitting diodes. Journal Physics D: Applied Physics, 2020, 53, 345501.	1.3	6
29	Overcoming the excessive compressive strain in AlGaIn epitaxy by introducing high Si-doping in AlN templates. Japanese Journal of Applied Physics, 2020, 59, 070904.	0.8	16
30	Analysis and Optimization of GaN Based Multi-Channels FinFETs. IEEE Nanotechnology Magazine, 2020, 19, 439-445.	1.1	8
31	Low-temperature carrier transport across InGaIn multiple quantum wells: Evidence of ballistic hole transport. Physical Review B, 2020, 101, .	1.1	6
32	A Thermoelectrically Cooled nBn Type-II Superlattices InAs/InAsSb/B ϵ AlAsSb Mid-Wave Infrared Detector. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900522.	0.8	4
33	Application of localization landscape theory and the $k^{\circ}\hat{\cdot}$ model for direct modeling of carrier transport in a type II superlattice InAs/InAsSb photoconductor system. Journal of Applied Physics, 2020, 127, .	1.1	16
34	AlGaIn-based deep ultraviolet light emitting diodes with magnesium delta-doped AlGaIn last barrier. Applied Physics Letters, 2020, 117, .	1.5	17
35	Barriers to carrier transport in multiple quantum well nitride-based c-plane green light emitting diodes. Physical Review Materials, 2020, 4, .	0.9	16
36	Revealing the mechanism of carrier transport in host-guest systems of organic materials with a modified Poisson and drift-diffusion solver. Physical Review Materials, 2020, 4, .	0.9	6

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37	Light Trapping Induced High Short-Circuit Current Density in III-Nitride Nanorods/Si (111) Heterojunction Solar Cells. <i>Nanoscale Research Letters</i> , 2020, 15, 167.	3.1	5
38	Dependence of carrier escape lifetimes on quantum barrier thickness in InGaN/GaN multiple quantum well photodetectors. <i>Optics Express</i> , 2020, 28, 23796.	1.7	15
39	Disorder effects in nitride semiconductors: impact on fundamental and device properties. <i>Nanophotonics</i> , 2020, 10, 3-21.	2.9	23
40	Analysis of the hysteresis effect in Perovskite solar cells for the traditional and inverted architectures. , 2020, , .		1
41	3D Self-Consistent Quantum Transport Simulation for GaAs Gate-All-Around Nanowire Field-Effect Transistor with Elastic and Inelastic Scattering Effects. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1800524.	0.8	1
42	Demonstration of the Very Long Wavelength Infrared Type-II Superlattice InAs/InAsSb GaAs Immersed Photodetector Operating at Thermoelectric Cooling. <i>IEEE Electron Device Letters</i> , 2019, 40, 1396-1398.	2.2	14
43	Theoretical modelling of X _{Bn} T2SLs InAs/InAsSb/B-AlAsSb mid-wave detector operating below thermoelectrical cooling. <i>Opto-electronics Review</i> , 2019, 27, 275-281.	2.4	1
44	Optimization of MAPbI ₃ -Based Perovskite Solar Cell With Textured Surface. <i>IEEE Journal of Photovoltaics</i> , 2019, 9, 1686-1692.	1.5	8
45	Thermoelectrically Cooled n _{Bn} T2SLs InAs/InAsSb/B-AlAsSb MWIR Detector. , 2019, , .		0
46	Interwell carrier transport in InGaN/(In)GaN multiple quantum wells. <i>Applied Physics Letters</i> , 2019, 114, .	1.5	21
47	Systematic investigation of the threshold voltage modulation of AlGaIn/GaN Schottky-gate Fin-HEMTs. <i>Journal of Applied Physics</i> , 2019, 125, 094502.	1.1	6
48	Modeling dislocation-related leakage currents in GaN p-n diodes. <i>Journal of Applied Physics</i> , 2019, 126, 245705.	1.1	6
49	Hybrid classical-quantum linear solver using Noisy Intermediate-Scale Quantum machines. <i>Scientific Reports</i> , 2019, 9, 16251.	1.6	20
50	Investigation of Electronic Properties of MoxW1â€ˆxS2 Alloy by Tight-binding Method for Interband transition. , 2019, , .		0
51	Optimization of MAPbI ₃ Perovskite Solar Cell with Nano Structures. , 2018, , .		0
52	Three dimensional simulation on the transport and quantum efficiency of UVC-LEDs with random alloy fluctuations. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	27
53	Different surface plasmon coupling behaviors of a surface Al nanoparticle between TE and TM polarizations in a deep-UV light-emitting diode. <i>Optics Express</i> , 2018, 26, 8340.	1.7	9
54	Nonpolar and semipolar LEDs. , 2018, , 273-295.		4

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55	Evidence of nanoscale Anderson localization induced by intrinsic compositional disorder in InGa _N /Ga _N quantum wells by scanning tunneling luminescence spectroscopy. <i>Physical Review B</i> , 2018, 98, .	1.1	28
56	Mode-Hopping Phenomena in the InGa _N -Based Core-Shell Nanorod Array Collective Lasing. <i>ACS Photonics</i> , 2018, 5, 2724-2729.	3.2	3
57	Electronic properties of MoS ₂ nanoribbon with strain using tight-binding method. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1600565.	0.7	11
58	Vertical transport through AlGa _N barriers in heterostructures grown by ammonia molecular beam epitaxy and metalorganic chemical vapor deposition. <i>Semiconductor Science and Technology</i> , 2017, 32, 025010.	1.0	11
59	Suppression of Current Collapse in Enhancement Mode Ga _N -Based HEMTs Using an AlGa _N /Ga _N /AlGa _N Double Heterostructure. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 1505-1510.	1.6	26
60	Three dimensional characterization of Ga _N -based light emitting diode grown on patterned sapphire substrate by confocal Raman and photoluminescence spectromicroscopy. <i>Scientific Reports</i> , 2017, 7, 45519.	1.6	17
61	A design of intermediate band solar cell for photon ratchet with multi-layer MoS ₂ nanoribbons. <i>Applied Physics Letters</i> , 2017, 110, .	1.5	12
62	Networking hole and electron hopping paths by Y-shaped host molecules: promoting blue phosphorescent organic light emitting diodes. <i>Journal of Materials Chemistry C</i> , 2017, 5, 3600-3608.	2.7	12
63	Transferring the bendable substrateless Ga _N LED grown on a thin C-rich SiC buffer layer to flexible dielectric and metallic plates. <i>Journal of Materials Chemistry C</i> , 2017, 5, 607-617.	2.7	30
64	Combining High Hole Concentration in p-Ga _N and High Mobility in u-Ga _N for High p-Type Conductivity in a p-Ga _N /u-Ga _N Alternating-Layer Nanostructure. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 115-120.	1.6	13
65	Localization landscape theory of disorder in semiconductors. I. Theory and modeling. <i>Physical Review B</i> , 2017, 95, .	1.1	81
66	Localization landscape theory of disorder in semiconductors. III. Application to carrier transport and recombination in light emitting diodes. <i>Physical Review B</i> , 2017, 95, .	1.1	95
67	Enhancing the Hole-Injection Efficiency of a Light-Emitting Diode by Increasing Mg Doping in the p-AlGa _N Electron-Blocking Layer. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 3226-3233.	1.6	7
68	Three dimensional compressive strain and its effect on optical properties of Ga _N -based light emitting diode grown on patterned sapphire substrate by confocal spectromicroscopy. , 2017, , .		0
69	Modeling of carrier transport and exciton diffusion in organic light emitting diodes with different doping effects. , 2017, , .		0
70	Optimized Design of Back-Contact Thin-Film GaAs Solar Cells. , 2017, , .		0
71	Modeling of carrier transport in organic light emitting diode with random dopant effects by two-dimensional simulation. <i>Optics Express</i> , 2017, 25, 25492.	1.7	8
72	Method for enhancing the favored transverse-electric-polarized emission of an AlGa _N deep-ultraviolet quantum well. <i>Optics Express</i> , 2017, 25, 26365.	1.7	10

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73	Back-contacted thin-film GaAs solar cells. , 2017, , .		0
74	Localization landscape theory of disorder in semiconductors. II. Urbach tails of disordered quantum well layers. Physical Review B, 2017, 95, .	1.1	78
75	Optimization of thermoelectric properties for rough nano-ridge GaAs/AlAs superlattice structure. AIP Advances, 2016, 6, 115201.	0.6	10
76	Analysis of the PEDOT:PSS/Si nanowire hybrid solar cell with a tail state model. Journal of Applied Physics, 2016, 120, .	1.1	15
77	3D numerical modeling of the carrier transport and radiative efficiency for InGaN/GaN light emitting diodes with V-shaped pits. AIP Advances, 2016, 6, .	0.6	35
78	Back-contacted thin-film GaAs solar cells. , 2016, , .		4
79	Modeling of random dopant effects of organic light emitting diode with two dimensional simulation. , 2016, , .		0
80	Numerical analysis and optimization of PEDOT:PSS/Si nanowire hybrid solar cells. , 2016, , .		0
81	Electronic properties of MoS ₂ nanoribbon with strain using tight binding method. , 2016, , .		0
82	Optimization of the gain curve of the InGaN blue light laser diode. , 2016, , .		1
83	Development of numerical modeling program for organic/inorganic hybrid solar cells by including tail/interfacial states models. , 2016, , .		0
84	Electronic properties of strained monolayer MoS ₂ using tight binding method. , 2016, , .		4
85	Study of percolation transport in the InGaN/AlGaIn LEDs with random alloy fluctuation. , 2015, , .		0
86	Development of quantum transport simulation model by considering phonon scattering in nanowire device. , 2015, , .		0
87	Designing of p-Al _x Ga _{1-x} N/Al _y Ga _{1-y} N super lattice structure as the p-contact and transparent layer in AlGaIn UVLEDs. , 2015, , .		0
88	3D finite element strain analysis of V-shaped pits in light emitting diodes. , 2015, , .		0
89	Electron transport in unipolar InGaIn/GaN multiple quantum well structures grown by NH ₃ molecular beam epitaxy. Journal of Applied Physics, 2015, 117, .	1.1	42
90	Investigation of carrier transport in nitride based LED by considering the random alloy fluctuation. , 2015, , .		0

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91	Modeling and optimization of p-AlGaIn super lattice structure as the p-contact and transparent layer in AlGaIn UVLEDs. Optics Express, 2015, 23, 32367.	1.7	9
92	The Effect of Tensile Strain on Optical Anisotropy and Exciton of m -Plane ZnO. IEEE Photonics Journal, 2015, 7, 1-8.	1.0	2
93	Optimization of all-back-contact GaAs solar cells. , 2015, , .		1
94	Impact of Gate Metal on the Performance of p-GaN/AlGaIn/GaN High Electron Mobility Transistors. IEEE Electron Device Letters, 2015, 36, 232-234.	2.2	105
95	Design of nano-pattern reflectors for thin-film solar cells based on three-dimensional optical and electrical modeling. , 2015, , .		1
96	Percolation transport study in nitride based LED by considering the random alloy fluctuation. Journal of Computational Electronics, 2015, 14, 416-424.	1.3	23
97	Numerical study of current spreading and light extraction in deep UV light-emitting diode. , 2015, , .		2
98	High optical power and low efficiency droop blue light-emitting diodes using compositionally step-graded InGaIn barrier. Electronics Letters, 2015, 51, 1187-1189.	0.5	21
99	Modeling for carrier transportation in organic light-emitting diode by considering effective tail states. , 2015, , .		0
100	Modeling for carrier transportation in organic light-emitting diode by considering effective tail states. , 2015, , .		0
101	Valence band states and polarized optical emission from nonpolar and semipolar III-nitride quantum well optoelectronic devices. Japanese Journal of Applied Physics, 2014, 53, 100206.	0.8	34
102	Nonpolar and semipolar LEDs. , 2014, , 250-275.		0
103	A review of non linear piezoelectricity in semiconductors. AIP Conference Proceedings, 2014, , .	0.3	12
104	Photoelectrochemical hydrogen generation with linear gradient Al composition dodecagon faceted AlGaIn/n-GaN electrode. Optics Express, 2014, 22, A1853.	1.7	4
105	The optimization study of textured a-Si:H solar cells. Journal of Renewable and Sustainable Energy, 2014, 6, 023111.	0.8	10
106	Design of anti-ring back reflectors for thin-film solar cells based on three-dimensional optical and electrical modeling. Applied Physics Letters, 2014, 105, 061108.	1.5	6
107	Thermoelectric characteristic of the rough InN/GaN core-shell nanowires. Journal of Applied Physics, 2014, 116, 103707.	1.1	9
108	The influence of random indium alloy fluctuations in indium gallium nitride quantum wells on the device behavior. Journal of Applied Physics, 2014, 116, .	1.1	124

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109	Design of light trapping nanopatterned solar cells based on three-dimensional optical and electrical modeling. , 2014, , .		0
110	Efficiency enhancement of thin-film a-Si:H solar cell with periodic anti-ring back reflector. , 2014, , .		0
111	Mechanisms of the Asymmetric Light Output Enhancements in a -Plane GaN Light-Emitting Diodes With Photonic Crystals. IEEE Journal of Quantum Electronics, 2014, 50, 1-6.	1.0	3
112	The optimization of textured a-Si:H solar cells with a fully three-dimensional simulation. , 2014, , .		1
113	Influence of nanoscale indium fluctuation in the InGaN quantum-well LED to the efficiency droop with a fully 3D simulation model. Proceedings of SPIE, 2014, , .	0.8	1
114	Efficiency dip observed with InGaN-based multiple quantum well solar cells. Optics Express, 2014, 22, A1753.	1.7	7
115	Characteristics of large-scale nanohole arrays for thin-silicon photovoltaics. Progress in Photovoltaics: Research and Applications, 2014, 22, 452-461.	4.4	47
116	Polarization ratio enhancement of a -plane GaN light emitting diodes by asymmetric two-dimensional photonic crystals. Journal of Applied Physics, 2014, 115, .	1.1	9
117	Study on the Optimization for Current Spreading Effect of Lateral GaN/InGaN LEDs. IEEE Transactions on Electron Devices, 2014, 61, 511-517.	1.6	23
118	Thermal Effects in a Bendable InGaN/GaN Quantum-Well Light-Emitting Diode. IEEE Photonics Technology Letters, 2014, 26, 1442-1445.	1.3	2
119	High-electron-mobility GaN grown on free-standing GaN templates by ammonia-based molecular beam epitaxy. Journal of Applied Physics, 2014, 115, .	1.1	103
120	Atomic-scale nanofacet structure in semipolar $(20\bar{2}1)$ and $(20\bar{2}1)$ InGaN single quantum wells. Applied Physics Express, 2014, 7, 025503.	1.1	14
121	GaN-Based Dual-Color LEDs With p -Type Insertion Layer for Controlling the Ratio of Two-Color Intensities. IEEE Transactions on Electron Devices, 2013, 60, 2821-2826.	1.6	6
122	Enhancement of efficiency of InGaN-based light emitting diodes through strain and piezoelectric field management. Journal of Applied Physics, 2013, 114, 073104.	1.1	18
123	Study of light emission polarization properties of semipolar InGaN/GaN quantum well under different strain conditions. , 2013, , .		0
124	Influences of indium fluctuation to the carrier transport, auger recombination, and efficiency droop. , 2013, , .		3
125	Three dimensional numerical study on the efficiency of a core-shell InGaN/GaN multiple quantum well nanowire LED. , 2013, , .		0
126	On the Efficiency Decrease of the GaN Light-Emitting Nanorod Arrays. IEEE Journal of Quantum Electronics, 2013, 49, 224-231.	1.0	12

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127	Projected Efficiency of Polarization-Matched p-In _x Ga _{1-x} N/n-GaN Double Heterojunction Solar Cells. IEEE Journal of Photovoltaics, 2013, 3, 985-990.	1.5	10
128	Studying the short channel effect in the scaling of the AlGaIn/GaN nanowire transistors. Journal of Applied Physics, 2013, 113, 214501.	1.1	17
129	Three dimensional numerical study on the efficiency of a core-shell InGaIn/GaN multiple quantum well nanowire light-emitting diodes. Journal of Applied Physics, 2013, 113, 183104.	1.1	27
130	The operation principle of the well in quantum dot stack infrared photodetector. Journal of Applied Physics, 2013, 114, 244504.	1.1	3
131	DC and RF Characteristics of Ga ₂ O ₃ /GaN Single Nanowire MOSFET. ECS Transactions, 2013, 50, 75-79.	0.3	1
132	Surface-plasmon-coupled emission enhancement of a quantum well with a metal nanoparticle embedded in a light-emitting diode. Journal of the Optical Society of America B: Optical Physics, 2013, 30, 2599.	0.9	23
133	Unipolar vertical transport in GaN/AlGaIn/GaN heterostructures. Applied Physics Letters, 2013, 103, .	1.5	49
134	Scaling performance of Ga ₂ O ₃ /GaN nanowire field effect transistor. Journal of Applied Physics, 2013, 114, 163706.	1.1	6
135	Semipolar (2021), Single-Quantum-Well Red Light-Emitting Diodes with a Low Forward Voltage. Japanese Journal of Applied Physics, 2013, 52, 08JC08.	0.8	27
136	Atom Probe Tomography of III-Nitrides Based Semiconducting Devices. Microscopy and Microanalysis, 2013, 19, 956-957.	0.2	0
137	GaN-Based Dual Color LEDs with P-Type Insertion Layer for Balancing Two-Color Intensities. , 2013, , .		1
138	Scaling of GaN single nanowire MOSFET with cut-off frequency 150GHz. , 2012, , .		1
139	Intersubband and intrasubband transition in InGaIn quantum dot for solar cell application. , 2012, , .		0
140	Study of optical anisotropy in nonpolar and semipolar AlGaIn quantum well deep ultraviolet light emission diode. Journal of Applied Physics, 2012, 112, .	1.1	24
141	The effect of tailoring electron/hole blocking layers on the photovoltaic performance of the single junction solar cells. , 2012, , .		0
142	Fabrication and modeling of large-scale silicon nanowire solar cells for thin-film photovoltaics. , 2012, , .		3
143	Carrier escape mechanism dependence on barrier thickness and temperature in InGaIn quantum well solar cells. Applied Physics Letters, 2012, 101, .	1.5	72
144	Short channel effects on gallium nitride/gallium oxide nanowire transistors. Applied Physics Letters, 2012, 101, 183501.	1.5	20

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145	Numerical modeling of In _x Ga _{1-x} silicon multi-junction tandem solar cell. , 2012, , .		0
146	Thin 3D Multiplication Regions in Plasmonically Enhanced Nanopillar Avalanche Detectors. Nano Letters, 2012, 12, 6448-6452.	4.5	39
147	Analyzing the physical properties of InGaN multiple quantum well light emitting diodes from nano scale structure. Applied Physics Letters, 2012, 101, 083505.	1.5	101
148	Performance and polarization effects in (112 $\bar{2}$) long wavelength light emitting diodes grown on stress relaxed InGaN buffer layers. Applied Physics Letters, 2012, 101, 121106.	1.5	53
149	Transition rate in the InGaN quantum dot intermediate-band solar cell. , 2012, , .		4
150	Influence of polarity on carrier transport in semipolar (20 $\bar{1}$) and (20 $\bar{2}$) multiple-quantum-well light-emitting diodes. Applied Physics Letters, 2012, 100, .	1.5	54
151	Study on the Current Spreading Effect and Light Extraction Enhancement of Vertical GaN/InGaN LEDs. IEEE Transactions on Electron Devices, 2012, 59, 400-407.	1.6	111
152	Study of Optical Anisotropy of c-plane/m-plane Ultra-violet LED and Laser Diode by k \cdot p Method. , 2012, , .		1
153	Influences of Indium Fluctuation to carrier transport and the Current-voltage Turn-on Behavior in the InGaN Quantum Well LEDs. , 2012, , .		0
154	Electrical properties of modulation-doped rf-sputtered polycrystalline MgZnO/ZnO heterostructures. Journal Physics D: Applied Physics, 2011, 44, 455101.	1.3	24
155	Numerical Study of Scaling Issues in Graphene Nanoribbon Transistors. Materials Research Society Symposia Proceedings, 2011, 1344, 1.	0.1	3
156	X-ray absorption fine-structure and optical studies of AlZnO nano-thin films grown on sapphire by pulsed laser deposition. Proceedings of SPIE, 2011, , .	0.8	0
157	Investigation of the strain induced optical transition energy shift of the GaN nanorod light emitting diode arrays. Optics Express, 2011, 19, A900.	1.7	12
158	2-Dimensional optoelectronic simulation for nanostructured organic-inorganic hybrid solar cells. , 2011, , .		0
159	Current spreading effect in vertical GaN/InGaN LEDs. Proceedings of SPIE, 2011, , .	0.8	1
160	Study of thermoelectric properties of indium nitride nanowire. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1562-1565.	0.8	10
161	Study of carrier dynamics and radiative efficiency in InGaN/GaN LEDs with Monte Carlo method. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2393-2395.	0.8	6
162	Transport properties of gallium nitride nanowire metal-oxide-semiconductor transistor. Applied Physics Letters, 2011, 99, .	1.5	11

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163	Optical Properties of the Partially Strain Relaxed InGaN/GaN Light-Emitting Diodes Induced by p-Type GaN Surface Texturing. IEEE Electron Device Letters, 2011, 32, 182-184.	2.2	20
164	Study of thermoelectric properties of InGaN/GaN superlattice. Materials Research Society Symposia Proceedings, 2011, 1329, 1.	0.1	0
165	Abnormal polarization switching phenomenon in a-plane Al _x Ga _{1-x} N. , 2011, , .		0
166	Role of interface roughness on lateral transport in InGaN/GaN LEDs: diffusion length, dislocation spacing, and radiative efficiency. Proceedings of SPIE, 2010, , .	0.8	1
167	Mobility Enhancement of Polycrystalline MgZnO/ZnO Thin Film Layers With Modulation Doping and Polarization Effects. IEEE Transactions on Electron Devices, 2010, 57, 696-703.	1.6	51
168	Study of Light Emission Enhancement in Nanostructured InGaN/GaN Quantum Wells. IEEE Journal of Quantum Electronics, 2010, 46, 884-889.	1.0	7
169	Light emission polarization properties of strained (11 $\bar{2}$ 0) semipolar InGaN quantum well. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1859-1862.	0.8	0
170	Study of Polarization Properties of Light Emitted from Tensile Strained InGaN/AlInN Quantum Well. , 2010, , .		0
171	Strain-enhanced photoluminescence from Ge direct transition. Applied Physics Letters, 2010, 96, .	1.5	78
172	75GHz Ga ₂ O ₃ /GaN Single Nanowire Metal- Oxide-Semiconductor Field-Effect Transistors. , 2010, , .		1
173	100GHz depletion-mode Ga ₂ O ₃ /GaN single nanowire MOSFET by photo-enhanced chemical oxidation method. , 2010, , .		3
174	Two dimensional electron gases in polycrystalline MgZnO/ZnO heterostructures grown by rf-sputtering process. Journal of Applied Physics, 2010, 108, .	1.1	71
175	Light emission polarization properties of semipolar InGaN/GaN quantum well. Journal of Applied Physics, 2010, 107, 053112.	1.1	34
176	A study of the role of dislocation density, indium composition on the radiative efficiency in InGaN/GaN polar and nonpolar light-emitting diodes using drift-diffusion coupled with a Monte Carlo method. Journal of Applied Physics, 2010, 108, .	1.1	17
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